Silicon P-Channel MOS FET

HITACHI

ADE-208-143

Application

Low frequency power amplifier

Complementary pair with 2SK2220, 2SK2221

Features

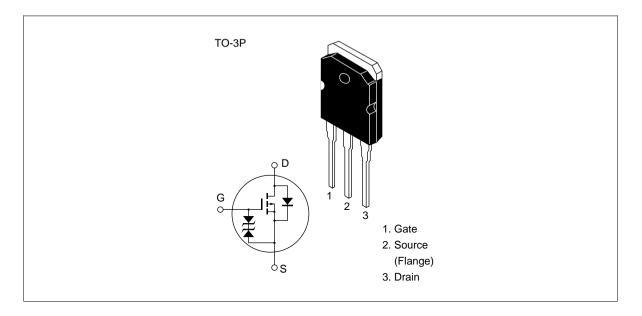
- High power gain
- Excellent frequency response
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes

Ordering Information

Type No.	V_{DSX}	
2SJ351	–180 V	_
2SJ352	–200 V	



Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

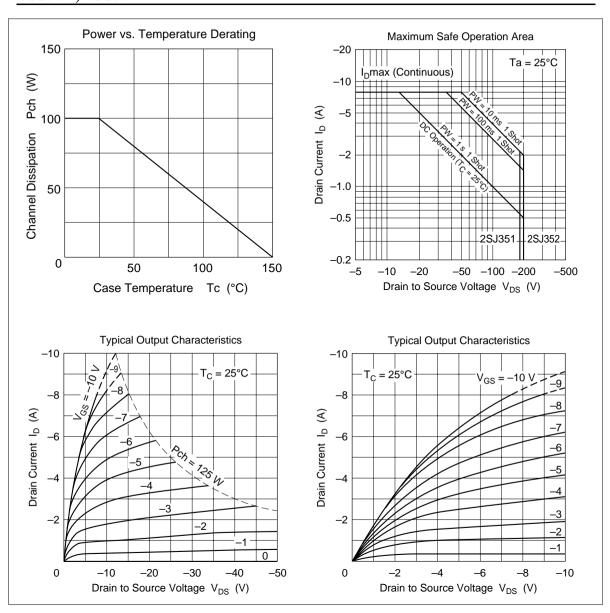
Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ351	$V_{\scriptscriptstyle DSX}$	-180	V
	2SJ352		-200	
Gate to source voltage		V_{GSS}	±20	V
Drain current		I _D	-8	A
Body to drain diode reverse drain current		I _{DR}	-8	A
Channel dissipation		Pch*1	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

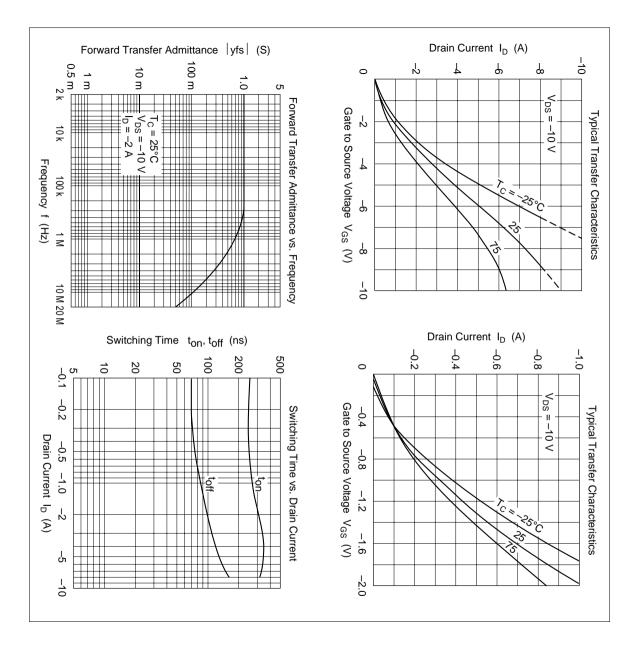
Note: 1. Value at $T_c = 25^{\circ}C$

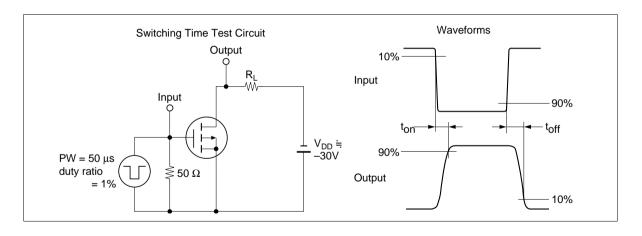
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SJ351	$V_{(BR)DSX}$	-180	_	_	٧	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$
breakdown voltage	2SJ352		-200	_	_		
Gate to source break voltage	kdown	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source cutof	f voltage	$V_{GS(off)}$	-0.15	_	-1.45	V	$I_D = -100 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain to source satu voltage	ration	$V_{DS(sat)}$	_	_	-12	V	$I_D = -8 \text{ A}, V_{GD} = 0^{*1}$
Forward transfer adr	mittance	$ y_{fs} $	0.7	1.0	1.4	S	$I_D = -3 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance		Ciss	_	800	_	pF	$V_{GS} = 5 \text{ V}, V_{DS} = -10 \text{ V},$
Output capacitance		Coss	_	1000	_	pF	f = 1 MHz
Reverse transfer cap	oacitance	Crss	_	18	_	pF	
Turn-on time		t _{on}	_	320	_	ns	$V_{DD} = -30 \text{ V}, I_{D} = -4 \text{ A}$
Turn-off time		t _{off}	_	120	_	ns	

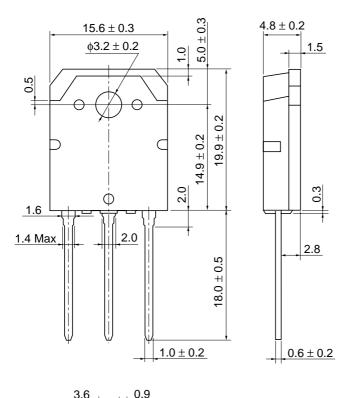
Note: 1. Pulse test

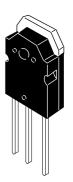






Unit: mm





		3.0		1	. 0.0	_		
				-	1.1	.0		
	Œ					=1		
5.45 ± 0	0.5		-			5.	45 ±	0.5

Hitachi Code	TO-3P
JEDEC	
EIAJ	Conforms
Weight (reference value)	5.0 g

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